

Amendments to the Claims

Claims 1-33 (Cancelled).

34. (Currently amended) A bit line contact comprising:

a first dielectric sidewall spacer formed in an opening and coating an interior sidewall of the opening, the opening extending to a node on a substrate, the first dielectric sidewall spacer comprising a first material;

a second dielectric sidewall spacer formed in the opening and coating an interior sidewall of the first dielectric sidewall spacer, the second dielectric sidewall spacer comprising a second material having a lower relative dielectric constant than the first material; and

a conductive plug formed within an interior sidewall of the second dielectric sidewall spacer and extending through the opening to the node.

35. (Cancelled)

36. (Original) The bit line contact of claim 34, wherein the conductive plug comprises doped polysilicon.

37. (Original) The bit line contact of claim 34, wherein the contact is laterally surrounded by six capacitors.

38. (Cancelled)

39. (Previously presented) The bit line contact of claim 34, wherein the first dielectric sidewall spacer comprises silicon nitride.

40. (Previously presented) The bit line contact of claim 34, wherein the second dielectric sidewall spacer comprises silicon dioxide.

41. (Previously presented) The bit line contact of claim 34, wherein the second dielectric sidewall spacer is thicker than the first dielectric sidewall spacer.

42. (New) A bit line contact comprising:
a bit line contact opening having a base surface and a pair of opposing interior sidewalls;
a pair of first dielectric sidewall spacers coating the pair of interior sidewalls;
a pair of second dielectric sidewall spacers formed in the opening and coating the first dielectric sidewall spacers; and
a conductive plug within the opening, the opening being substantially filled by the conductive plug, the pair of first dielectric spacers and the pair of second dielectric spacers.

43. (New) The bit line contact of claim 42, wherein the pair of first dielectric sidewall spacers comprises a first material, and the pair of second dielectric sidewall

spacers comprises a second material, the second material having a lower dielectric constant than the first material.

44. (New) The bit line contact of claim 42 wherein the pair of first dielectric sidewall spacers comprises silicon nitride.